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General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- \bullet High density cell design for low $R_{\text{DS}(\text{ON})}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Product Summary

V _{DS}	40V
R _{DS(on)@10V}	< 5.5mΩ
I _D	60A





Applications

- Power switching application
- Uninterruptible power supply
- DC-DC convertor

FDIN	J000-0L			
8 7 6 5 5 6 7 1 2 3 4 4 3 2	8	D 80 		D50

■ Absolute Maximum Ratings (T_A=25 °C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-source Voltage		V _{DS}	40	V	
Gate-source Voltage		V _{GS}	±20	V	
Drain Current	T _c =25°C		60		
	Tc=70°C	ID	39	A	
Pulsed Drain Current ^A		I _{DM}	240	А	
Avalanche energy ^B		EAS	85	mJ	
	T _c =25℃		40	w	
	T _c =70°C	PD	30		
Junction and Storage Temperature	Range	T _J ,T _{STG}	-55~+150	°C	





HXMS40N55LNA SGT N-Channel Enhancement Mode Field Effect Transistor

■ Electrical Characteristics (TJ=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Мах	Units	
Static Parameter							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250µA	40	-	-	V	
		V_{GS} = 0V, I _D =1mA	40	-	-	V	
Zana Osta Malta na Dusia Osmant	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μΑ	
Zero Gate voltage Drain Current		V _{DS} =40V, V _{GS} =0V, Tj=150℃	-	-	100		
Gate-Body Leakage Current	lgss	V_{GS} = ±20V, V_{DS} =0V	-	-	±100	nA	
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D =250 μ A	1.0	1.55	2.5	V	
Static Drain-Source On-Resistance	6	V_{GS} =10V, I_D =10A	-	4.5	5.5		
	RDS(ON)	V _{GS} =4.5V, I _D =8A	-	6.8	8.5	mΩ	
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V	-	-	1.2	V	
Gate resistance	R _G	f=1MHz	-	3.5	-	Ω	
Maximum Body-Diode Continuous Current	ls		-	-	36	А	
Dynamic Parameters							
Input Capacitance	C _{iss}		600	948	1200		
Output Capacitance	Coss	V_{DS} =20V, V_{GS} =0V, f=1MHz	300	555	800	pF	
Reverse Transfer Capacitance	Crss		2	31	70		
Switching Parameters							
Total Gate Charge	Qg		10	17	30		
Gate-Source Charge	Q _{gs}	V_{GS} =10V, V_{DS} =20V, I_{D} =50A	1	4.5	10	nC	
Gate-Drain Charge	Q_{gd}		0.5	2	10		
Reverse Recovery Charge	Qrr	504 K/K (000)	-	22	-	nC	
Reverse Recovery Time	trr	1F-50A, di/dl-100A/us	-	40	-	ns	
Turn-on Delay Time	t _{D(on)}		-	6.5	-		
Turn-on Rise Time	tr	V _{GS} =10V, V _{DD} =20V, I _D =50A	-	2.7	-	na	
Turn-off Delay Time	t _{D(off)}	R _{GEN} =3Ω	-	26	-	IIS	
Turn-off fall Time	t _f		-	3.6	-		

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_G=10V, R_G=25Ω, L=0.5 mH

C. Pd is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.





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■Typical Electrical and Thermal Characteristics Diagrams





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Package Outline Dimensions



Suggested Solder Pad Layout



Marking Information



"MHCHXM" = Product Logo				
"Marking Code" = The Following				
"XXXX" = Date Code Marking				

	5
Marking Code	Part Number
S40N55LNA	HXMS40N55LNA





The Orientation Of The Product In The Carrier Tape



Packing Information

Packaging	Part Number	Quantity(pcs)	Size(mm)
Reel	Reel	5000	Ф330×ТНК15
	Inner Box	10000	L355×W335×H48
	Outer Box	80000	L415×W375×H360

Packaging:Reel







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